Unit: mm

TOSHIBA Field Effect Transistor Silicon P/N Channel MOS Type(π-MOSVI)

# SSM6L16FE

## **High Speed Switching Applications**

## **Analog Switch Applications**

Small package

Low on-resistance Q1:  $RDS(ON) = 4 \Omega \text{ (max) } (@VGS = 2.5 \text{ V})$ 

Q2:  $R_{DS(ON)} = 12 \Omega \text{ (max) } (@V_{GS} = -2.5 \text{ V})$ 

#### Q1 Absolute Maximum Ratings (Ta = 25°C)

Characteristics		Symbol	Rating	Unit
Drain-Source voltage		$V_{DSS}$	20	V
Gate-Source voltage		$V_{GSS}$	±10	٧
Drain current	DC	ΙD	100	mA
	Pulse	I <sub>DP</sub>	200	Ш

## Q2 Absolute Maximum Ratings (Ta = 25°C)

Characteristics		Symbol	Rating	Unit	
Drain-Source voltage		$V_{DSS}$	-20	V	
Gate-Source voltage		$V_{GSS}$	±10	V	
Drain current	DC	ΙD	-100	mA	
	Pulse	I <sub>DP</sub>	-200	IIIA	

# 1.6±0.05 1.2±0.05 1.6±0.05 $0.2\pm0.05$ $0.12\pm0.05$ 1: Source1 2: Gate1 3: Drain2 4: Source2 5: Gate2 6: Drain1 ES6 **JEDEC** JEITA **TOSHIBA** 2-2N1D

Weight: 3 mg (typ.)

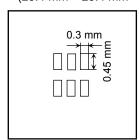
# Absolute Maximum Ratings (Q1, Q2 Common) (Ta = 25°C)

Characteristics	Symbol	Rating	Unit
Power dissipation	P <sub>D</sub> (Note 1)	150	mW
Channel temperature	T <sub>ch</sub>	150	°C
Storage temperature range	T <sub>stg</sub>	-55 to 150	°C

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

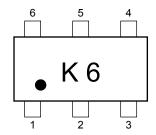
Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Note 1: Total rating, mounted on FR4 board (25.4 mm  $\times$  25.4 mm  $\times$  1.6 mm, Cu Pad: 0.135 mm $^2 \times$  6)

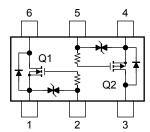


Start of commercial production 2002-03

## Marking



## **Equivalent Circuit (top view)**



## **Handling Precaution**

When handling individual devices (which are not yet mounted on a circuit board), ensure that the environment is protected against static electricity. Operators should wear anti-static clothing, and containers and other objects that come into direct contact with devices should be made of anti-static materials.

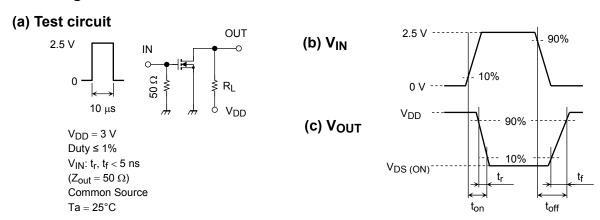
2

### Q1 Electrical Characteristics (Ta = 25°C)

Characteristic		Symbol	Test Condition	MIN.	TYP.	MAX.	UNIT
Gate leakage current		I <sub>GSS</sub>	$V_{GS} = \pm 10 \text{ V}, V_{DS} = 0$	_	_	±1	μА
Drain-Source breakdown voltage		V (BR) DSS	$I_D = 0.1 \text{ mA}, V_{GS} = 0$	20	_	_	V
Drain cut-off current		I <sub>DSS</sub>	V <sub>DS</sub> = 20 V, V <sub>GS</sub> = 0	_	_	1	μА
Gate threshold voltage		$V_{th}$	$V_{DS} = 3 \text{ V}, I_D = 0.1 \text{ mA}$	0.6	_	1.1	V
Forward transfer admittance		Y <sub>fs</sub>	$V_{DS} = 3 \text{ V}, I_D = 10 \text{ mA}$ (Note2)	40	_	_	mS
Drain-Source on-resistance		R <sub>DS</sub> (ON)	$I_D = 10 \text{ mA}, V_{GS} = 4 \text{ V}$ (Note2)	_	1.5	3.0	Ω
			$I_D = 10 \text{ mA}, V_{GS} = 2.5 \text{ V}$ (Note2)	_	2.2	4.0	
			$I_D = 1 \text{ mA}, V_{GS} = 1.5 \text{ V}$ (Note2)	_	5.2	15	
Input capacitance		C <sub>iss</sub>		_	9.3	_	pF
Reverse transfer capacitance		C <sub>rss</sub>	$V_{DS} = 3 \text{ V}, V_{GS} = 0, f = 1 \text{ MHz}$	_	4.5	_	pF
Output capacitance		C <sub>oss</sub>		_	9.8	_	pF
Switching time	Turn-on time	t <sub>on</sub>	$V_{DD} = 3 \text{ V}, I_D = 10 \text{ mA},$ $V_{GS} = 0 \text{ to } 2.5 \text{ V}$	_	70	_	no
	Turn-off time	t <sub>off</sub>		_	125	_	ns

Note2: Pulse test

## **Switching Time Test Circuit**



#### **Precaution**

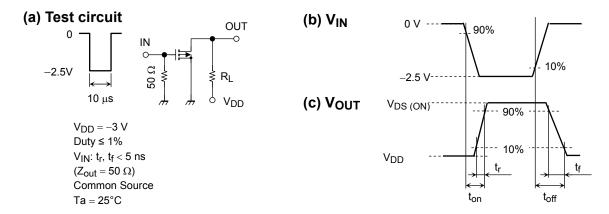
 $V_{th}$  can be expressed as the voltage between the gate and source when the low operating current value is ID = 0.1 mA for this product. For normal switching operation,  $V_{GS}$  (on) requires a higher voltage than  $V_{th}$  and  $V_{GS}$  (off) requires a lower voltage than  $V_{th}$ . (The relationship can be established as follows:  $V_{GS}$  (off)  $< V_{th} < V_{GS}$  (on).) Be sure to take this into consideration when using the device.

### Q2 Electrical Characteristics (Ta = 25°C)

Characteristic		Symbol	Test Condition	MIN.	TYP.	MAX.	UNIT
Gate leakage current		I <sub>GSS</sub>	$V_{GS} = \pm 10 \text{ V}, V_{DS} = 0$	_	_	±1	μА
Drain-Source breakdown voltage		V (BR) DSS	$I_D = -0.1 \text{ mA}, V_{GS} = 0$	-20	_	_	V
Drain cut-off current		I <sub>DSS</sub>	$V_{DS} = -20 \text{ V}, V_{GS} = 0$	_	_	-1	μА
Gate threshold voltage		V <sub>th</sub>	$V_{DS} = -3 \text{ V}, I_D = -0.1 \text{ mA}$	-0.6	_	-1.1	V
Forward transfer admittance		Y <sub>fs</sub>	$V_{DS} = -3 \text{ V}, I_D = -10 \text{ mA}$ (Note3)	25	_	_	mS
Drain-Source on-resistance		R <sub>DS</sub> (ON)	$I_D = -10 \text{ mA}, V_{GS} = -4 \text{ V}$ (Note3)	_	6	8	Ω
			$I_D = -10 \text{ mA}, V_{GS} = -2.5 \text{ V (Note3)}$	_	8	12	
			$I_D = -1 \text{ mA}, V_{GS} = -1.5 \text{ V}$ (Note3)	_	18	45	
Input capacitance		C <sub>iss</sub>		_	11	_	pF
Reverse transfer capacitance		C <sub>rss</sub>	$V_{DS} = -3 \text{ V}, V_{GS} = 0, f = 1 \text{ MHz}$	_	3.7	_	pF
Output capacitance		C <sub>oss</sub>		_	10	_	pF
Switching time	Turn-on time	t <sub>on</sub>	$V_{DD} = -3 \text{ V}, I_D = -10 \text{ mA},$	_	130	_	20
	Turn-off time	t <sub>off</sub>	$V_{GS} = 0 \text{ to } -2.5 \text{ V}$	_	190	_	ns

Note3: Pulse test

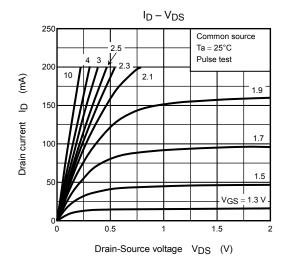
## **Switching Time Test Circuit**

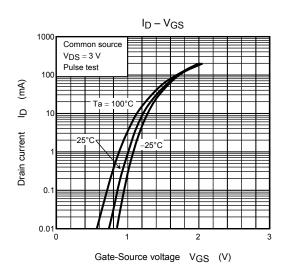


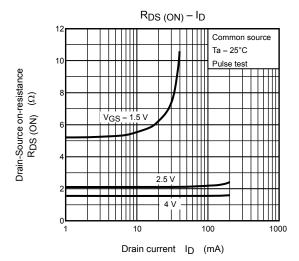
#### **Precaution**

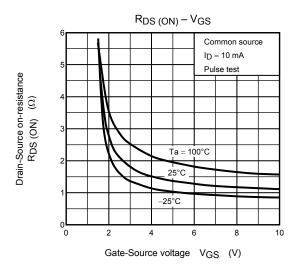
 $V_{th}$  can be expressed as the voltage between the gate and source when the low operating current value is  $I_D = -0.1$  mA for this product. For normal switching operation,  $V_{GS}$  (on) requires a higher voltage than  $V_{th}$  and  $V_{GS}$  (off) requires a lower voltage than  $V_{th}$ . (The relationship can be established as follows:  $V_{GS}$  (off)  $< V_{th} < V_{GS}$  (on).) Be sure to take this into consideration when using the device.

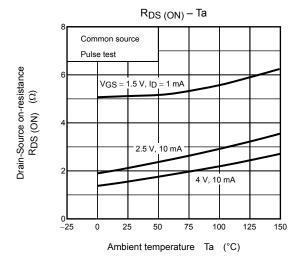
#### Q1 (N-ch MOSFET)

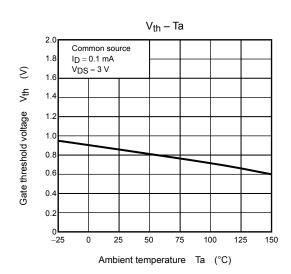






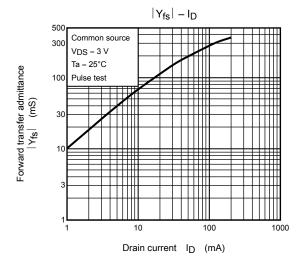


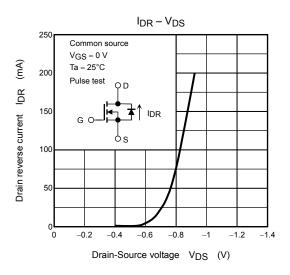


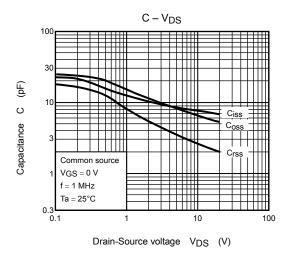


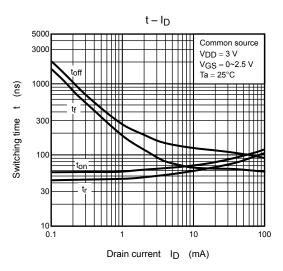
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#### Q1 (N-ch MOSFET)



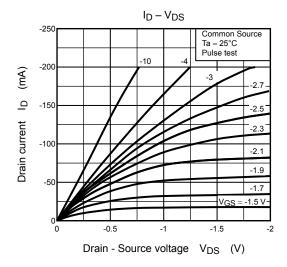


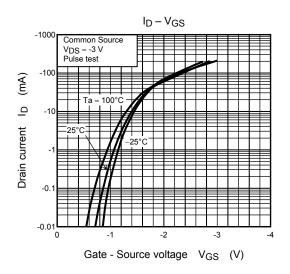


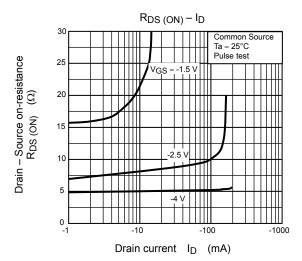


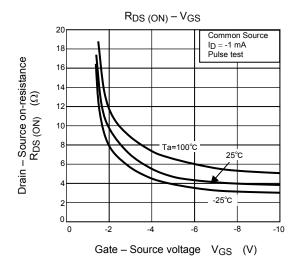
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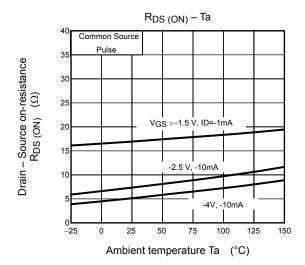
#### Q2 (P-ch MOSFET)

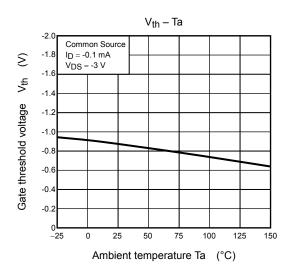




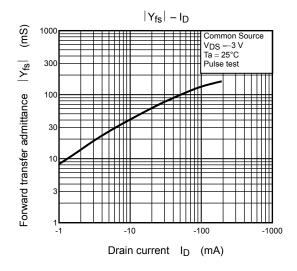


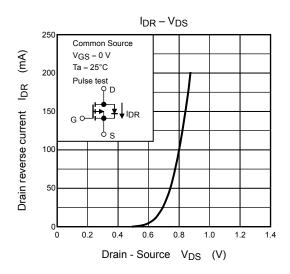


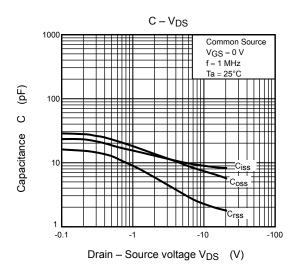


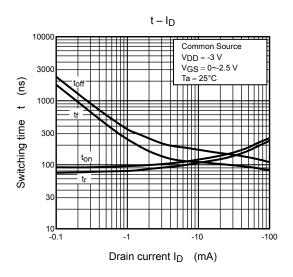


#### Q2 (P-ch MOSFET)

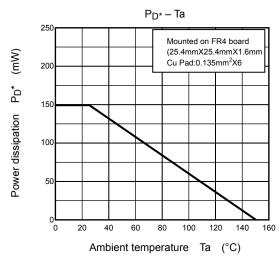








#### **Common Characteristics**



\*:Total rating

2014-03-01

8

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